Single 3-Input Positive AND-OR Gate

Check for Samples: SN74LVC1G0832

FEATURES

- **Available in the Texas Instruments NanoFree™ Package**
- **Supports 5-V V_{CC} Operation**
- **Inputs Accept Voltages to 5.5 V**
- **Provides Down Translation to V_{CC}**
- **Max t_{pd} of 5 ns at 3.3 V**
- **Low Power Consumption, 10-µA Max I_{CC}**
- **±24-mA Output Drive at 3.3 V**
- **Input Hysteresis Allows Slow Input Transition and Better Switching Noise Immunity at the Input (V_{hys} = 250 mV Typ @ 3.3 V)**
- **Can Be Used in Three Combinations:**
  - **AND-OR Gate**
  - **AND Gate**
  - **OR Gate**
- **I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **200-V Machine Model (A115-A)**
  - **1000-V Charged-Device Model (C101)**

DESCRIPTION

This device is designed for 1.65-V to 5.5-V V_{CC} operation.

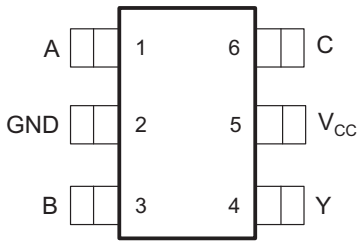
The SN74LVC1G0832 device is a single 3-input positive AND-OR gate. It performs the Boolean function Y = (A • B) + C in positive logic.

By tying one input to GND or V_{CC}, the SN74LVC1G0832 device offers two more functions. When C is tied to GND, this device performs as a 2−input AND gate (Y = A • B). When A is tied to V_{CC}, the device works as a 2−input OR gate (Y = B + C). This device also works as a 2−input OR gate when B is tied to V_{CC} (Y = A + C).

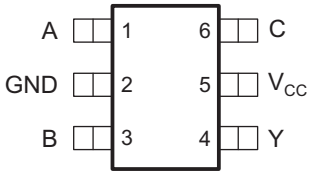
NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

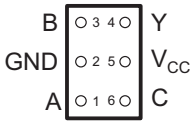
DBV PACKAGE
(TOP VIEW)



DCK PACKAGE
(TOP VIEW)



YZP PACKAGE
(BOTTOM VIEW)



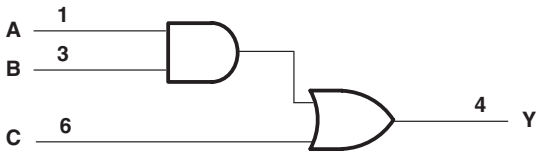
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Function Table(1)

INPUTS			OUTPUT
A	B	C	Y
X	X	H	H
H	H	X	H
X	L	L	L
L	X	L	L

(1) X = Valid H or L

Logic Diagram (Positive Logic)



Function Selection Table

LOGIC FUNCTION	FIGURE
2-Input AND Gate	Figure 1
2-Input OR Gate	Figure 2
Y = (A • B) + C	Figure 3

Logic Configurations

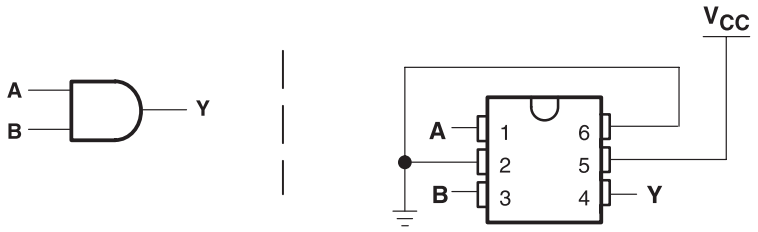


Figure 1. 2-Input AND Gate

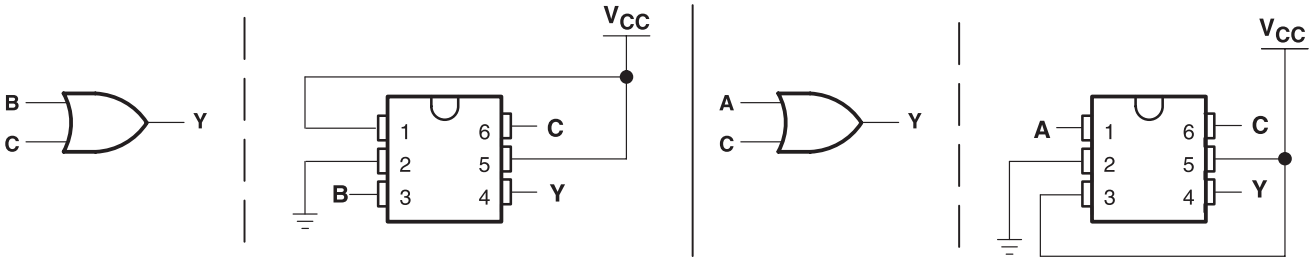


Figure 2. 2-Input OR Gate

Figure 3. Y = (A • B) + C

Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	6.5	V
V_I	Input voltage range(2)		–0.5	6.5	V
V_O	Voltage range applied to Y output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2)(3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
θ_{JA}	Package thermal impedance(4)	DBV package		215	°C/W
		DCK package		259	
		YZP package		123	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the recommended operating conditions table.
(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	5.5	V
		V_{CC} = 2.3 V to 2.7 V	1.7	5.5	
		V_{CC} = 3 V to 3.6 V	2	5.5	
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}	5.5	
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V	0	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	0		
		V_{CC} = 3 V to 3.6 V	0		
		V_{CC} = 4.5 V to 5.5 V	0		
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
Δt/Δv	Input transition rise or fall rate	V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V_{CC} = 3.3 V ± 0.3 V		10	
		V_{CC} = 5 V ± 0.5 V		5	
T_A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	–40°C to 85°C			–40°C to 125°C			UNIT
					MIN	TYP(1)	MAX	MIN	TYP(1)	MAX	
V_{OH}		I_{OH} = –100 µA	V_I = 5.5 V or GND	1.65 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
		I_{OH} = –4 mA		1.65 V	1.2			1.2			
		I_{OH} = –8 mA		2.3 V	1.9			1.9			
		I_{OH} = –16 mA		3 V	2.4			2.4			
		I_{OH} = –24 mA			2.3			2.3			
		I_{OH} = –32 mA		4.5 V	3.8			3.8			
V_{OL}		I_{OL} = 100 µA	V_I = 5.5 V or GND	1.65 V to 5.5 V			0.1			0.1	V
		I_{OL} = 4 mA		1.65 V			0.45			0.45	
		I_{OL} = 8 mA		2.3 V			0.3			0.3	
		I_{OL} = 16 mA		3 V			0.4			0.4	
		I_{OL} = 24 mA					0.55			0.55	
		I_{OL} = 32 mA		4.5 V			0.55			0.6	
I_I	A, B, or C inputs	V_I = 5.5 V or GND		0 to 5.5 V			±5			±5	µA
I_{off}		V_I or V_O = 5.5 V		0			±10			±10	µA
I_{CC}		V_I = 5.5 V or GND, I_O = 0		1.65 V to 5.5 V			10			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		3 V to 5.5 V			500			500	µA
C_i		V_I = V_{CC} or GND		3.3 V		7					pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

Switching Characteristics

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVC1G0832 –40°C to 85°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	3.7	14	2.4	7	1.7	5	1.2	3.4	ns

Switching Characteristics

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVC1G0832 –40°C to 85°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	2.5	17.5	1.8	7.6	1.8	5.9	1.3	4	ns

Switching Characteristics

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 5)

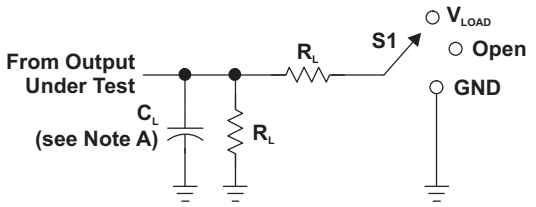
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74LVC1G0832 –40°C to 125°C								UNIT
			V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	2.5	17.5	1.8	7.6	1.8	5.9	1.3	4.5	ns

Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	f = 10 MHz	15	15	16	18	pF

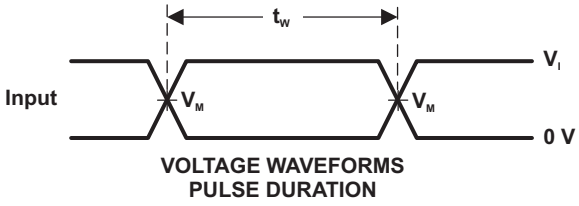
Parameter Measurement Information



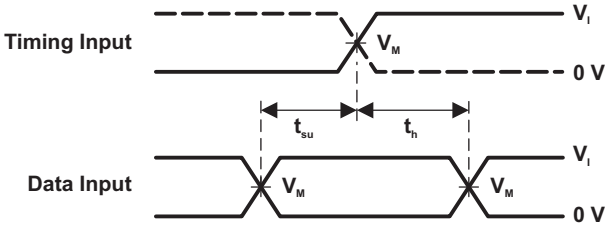
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

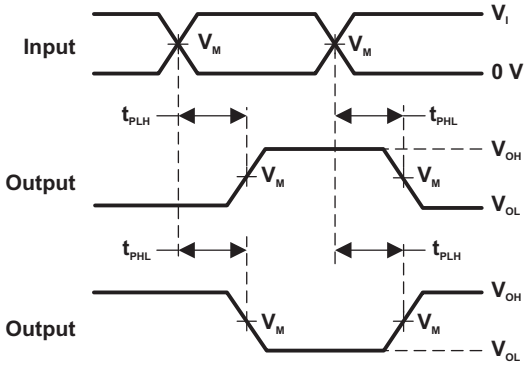
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 MΩ	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.3 V



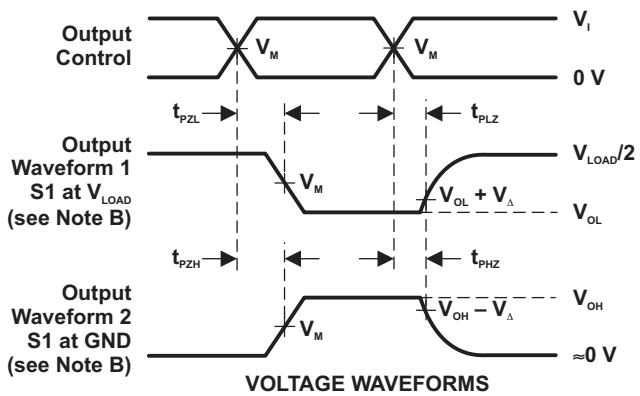
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

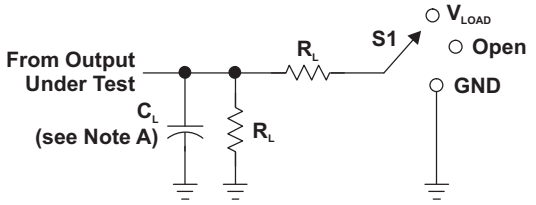


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

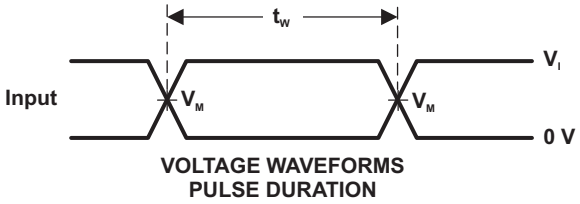
Parameter Measurement Information (continued)



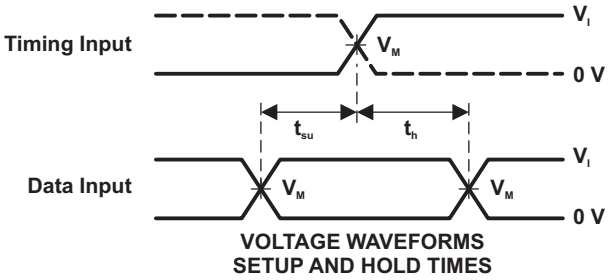
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

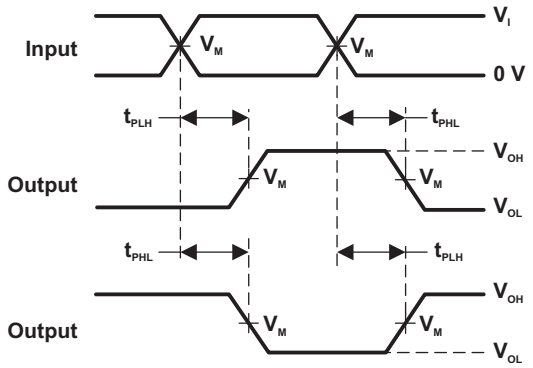
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	50 pF	500 Ω	0.3 V



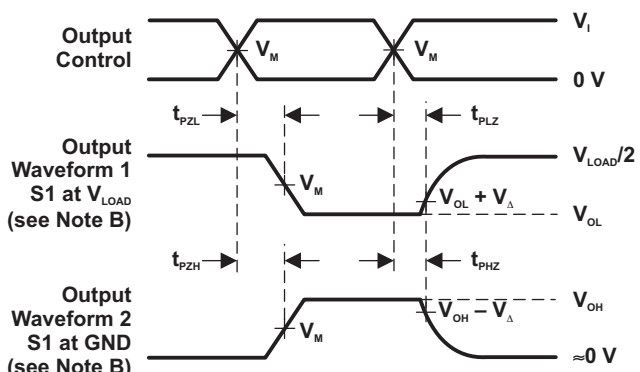
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



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LOW- AND HIGH-LEVEL ENABLING

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C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms

REVISION HISTORY

Changes from Revision C (January 2007) to Revision D	Page
• Updated document to new TI data sheet format.	1
• Updated Features.	1
• Added ESD warning.	2
• Updated operating temperature range.	5

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G0832DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CDCR	Samples
SN74LVC1G0832DBVT	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CDCR	Samples
SN74LVC1G0832DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(DCJ, DCR)	Samples
SN74LVC1G0832DCKT	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(DCJ, DCR)	Samples
SN74LVC1G0832YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	DCN	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

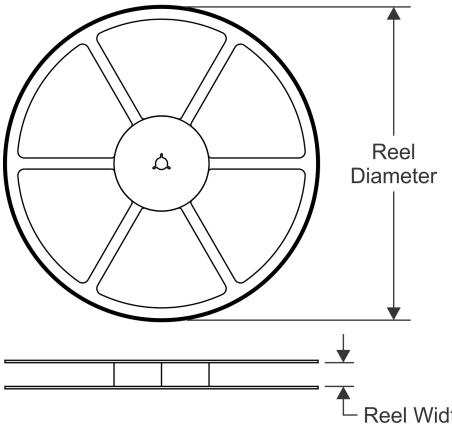
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

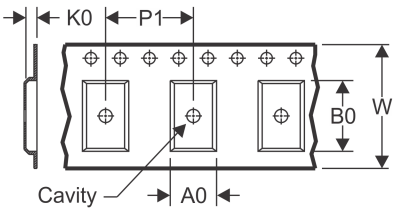
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

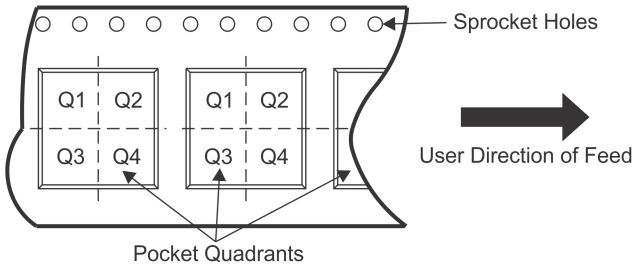


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

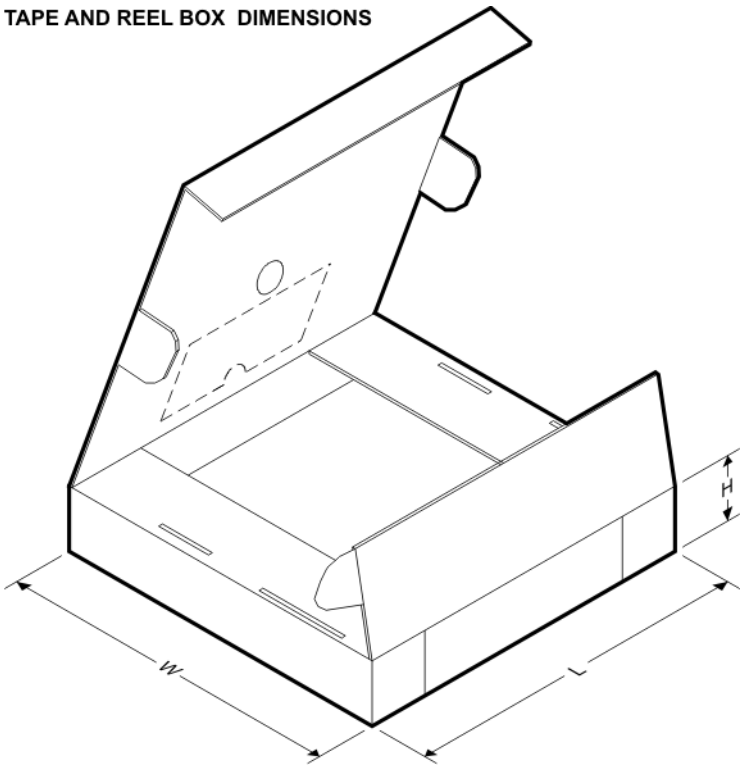
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G0832DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G0832DBVT	SOT-23	DBV	6	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G0832DCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74LVC1G0832DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G0832DCKT	SC70	DCK	6	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G0832DCKT	SC70	DCK	6	250	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74LVC1G0832YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

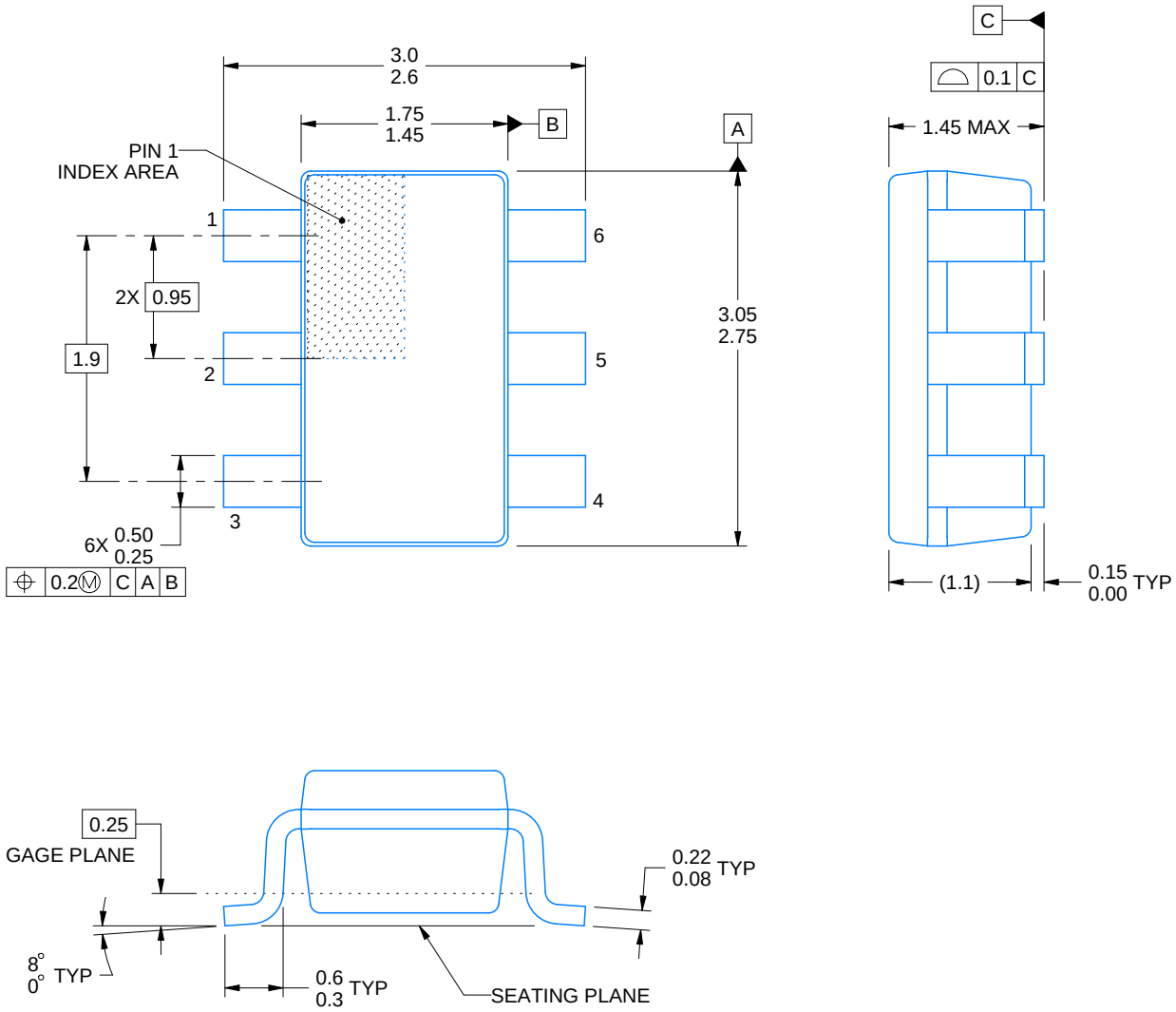
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G0832DBVR	SOT-23	DBV	6	3000	202.0	201.0	28.0
SN74LVC1G0832DBVT	SOT-23	DBV	6	250	202.0	201.0	28.0
SN74LVC1G0832DCKR	SC70	DCK	6	3000	202.0	201.0	28.0
SN74LVC1G0832DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1G0832DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC1G0832DCKT	SC70	DCK	6	250	202.0	201.0	28.0
SN74LVC1G0832YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0

PACKAGE OUTLINE

DBV0006A

SOT-23 - 1.45 mm max height

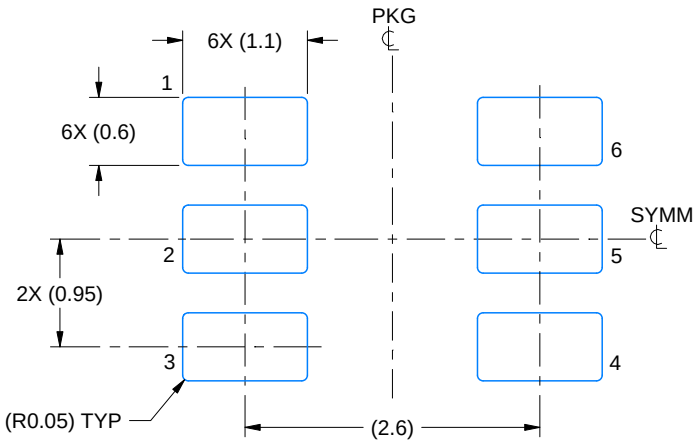
SMALL OUTLINE TRANSISTOR



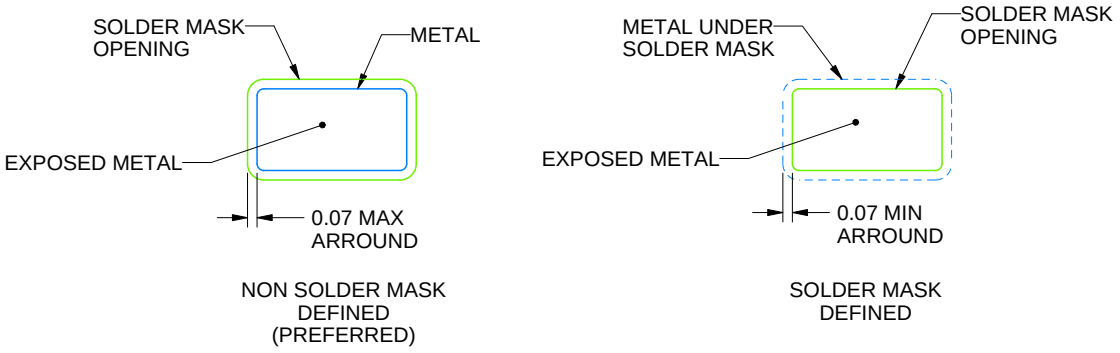
4214840/C 06/2021

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Refernce JEDEC MO-178.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

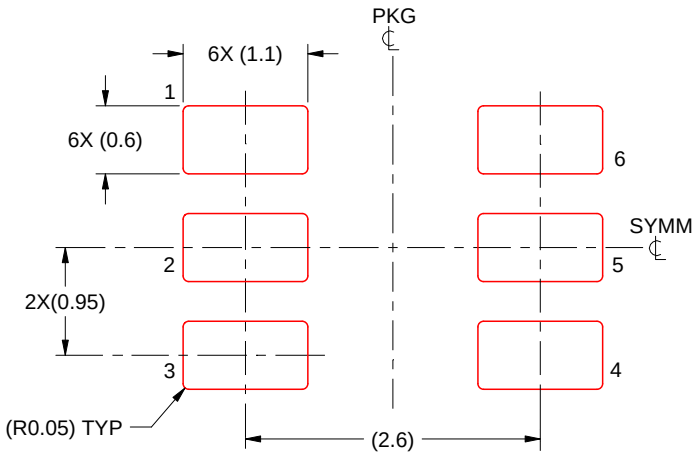


SOLDER MASK DETAILS

4214840/C 06/2021

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214840/C 06/2021

NOTES: (continued)

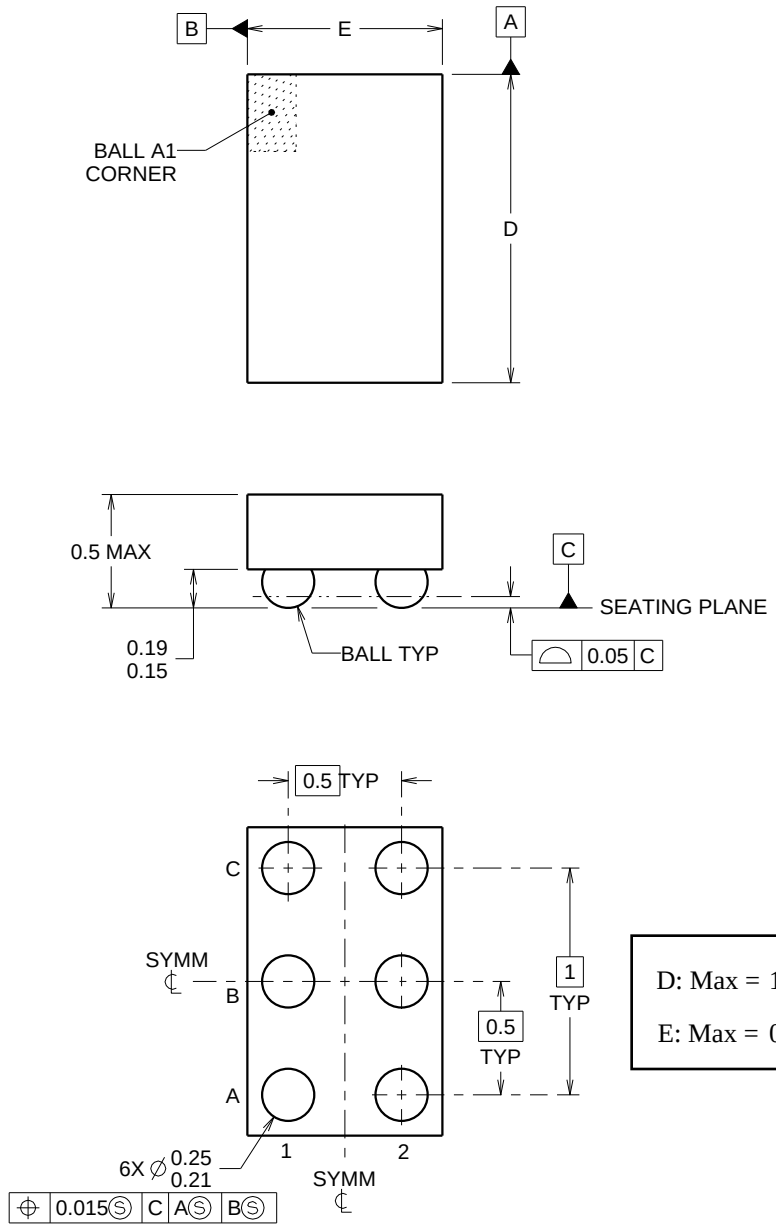
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

YZP0006

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



D: Max = 1.418 mm, Min =1.358 mm

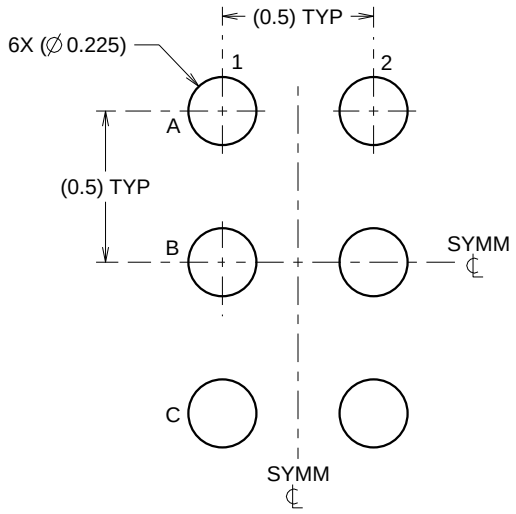
E: Max = 0.918 mm, Min =0.858 mm

4219524/A 06/2014

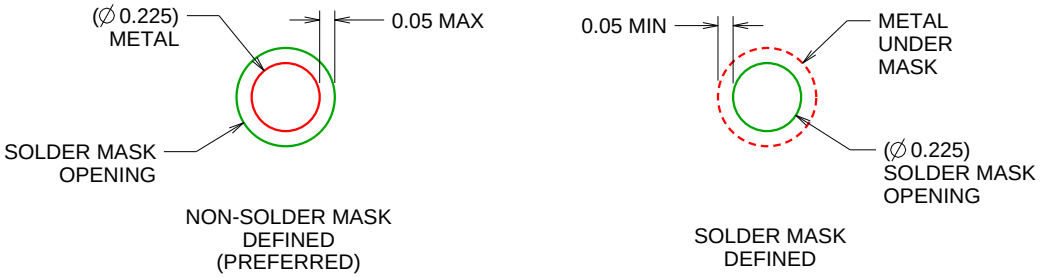
NOTES:

NanoFree Is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. NanoFree™ package configuration.



LAND PATTERN EXAMPLE
SCALE:40X

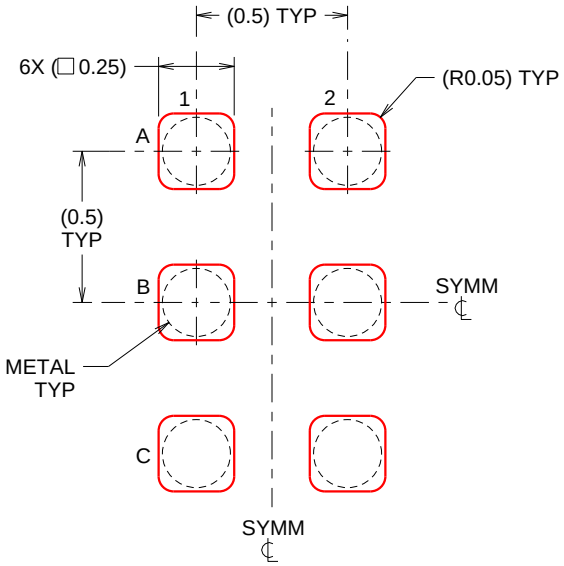


SOLDER MASK DETAILS
NOT TO SCALE

4219524/A 06/2014

NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



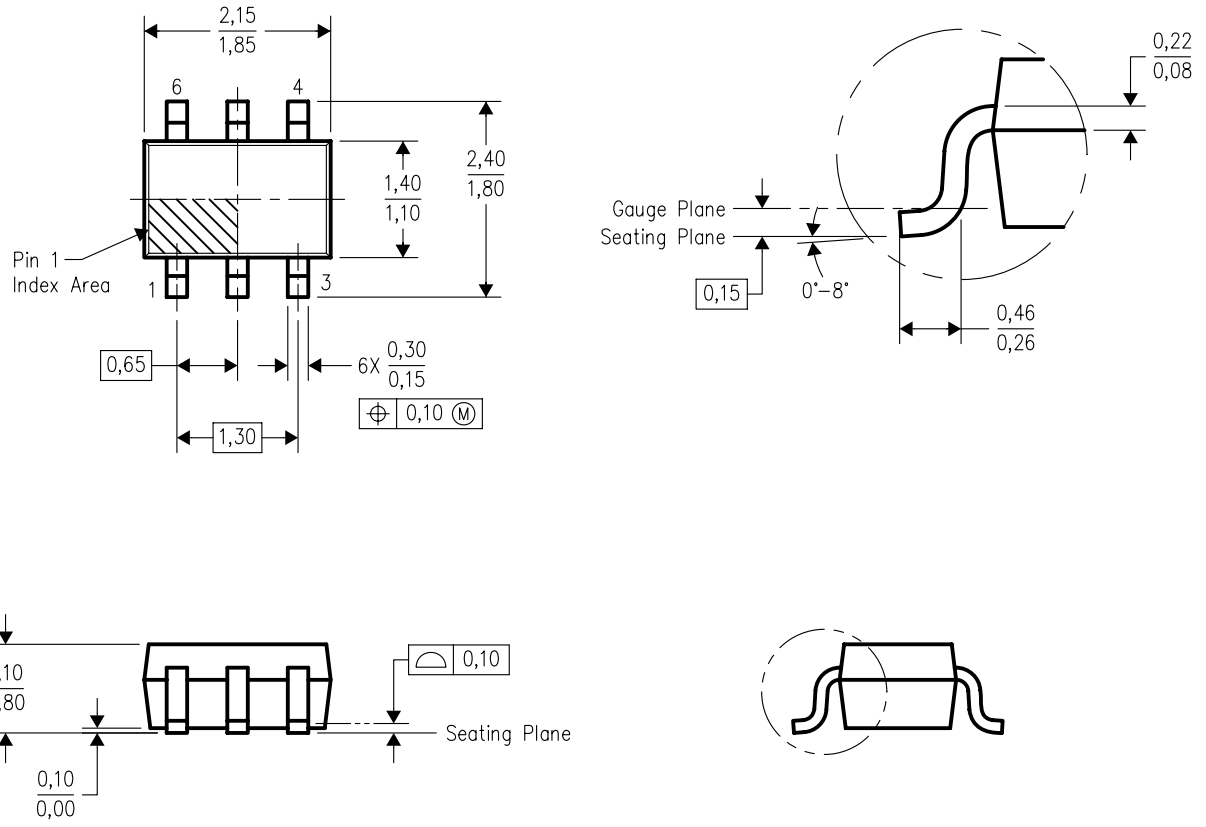
SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4219524/A 06/2014

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

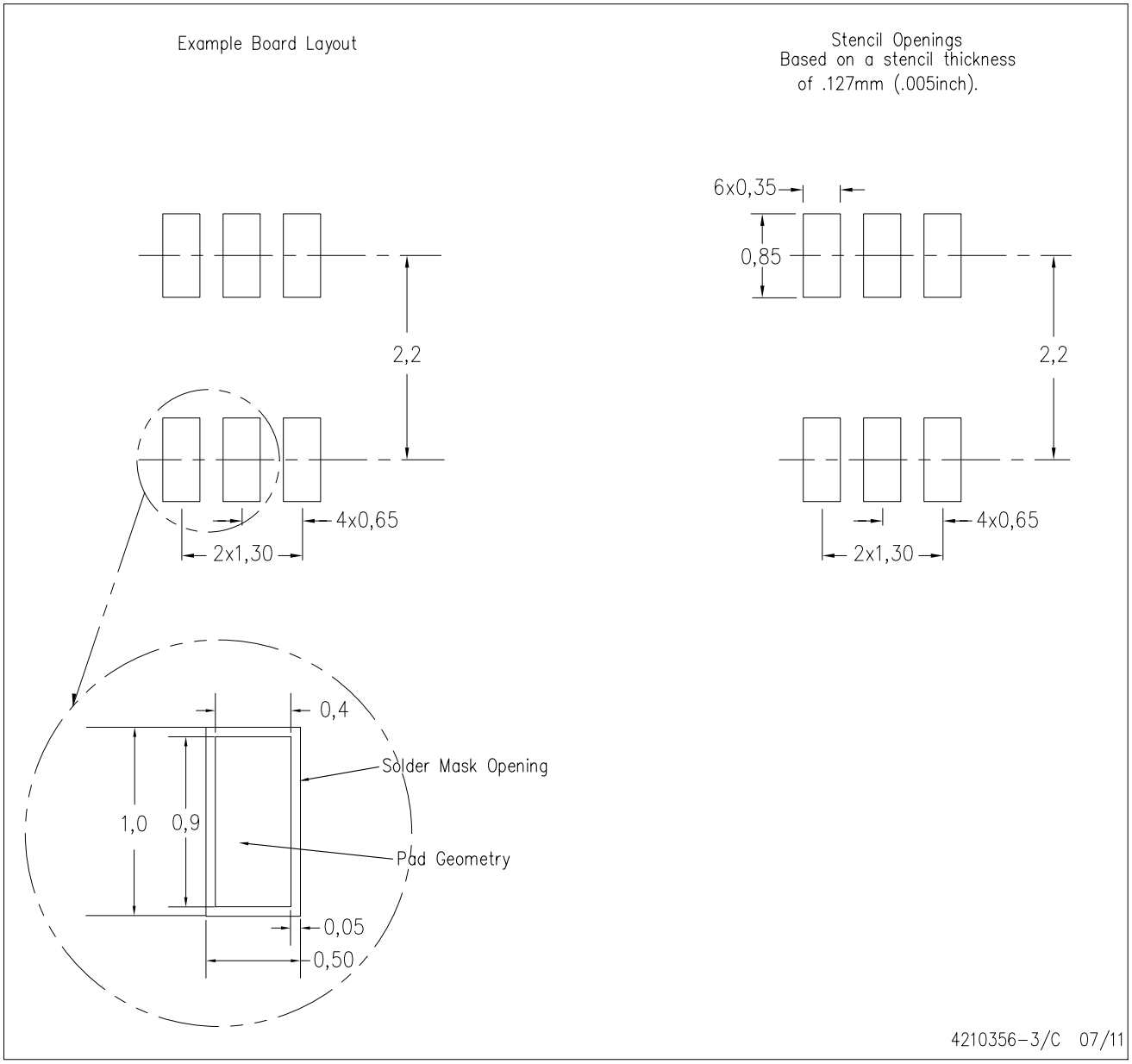
DCK (R–PDSO–G6) PLASTIC SMALL–OUTLINE PACKAGE



4093553–4/G 01/2007

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AB.

DCK (R–PDSO–G6) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

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